

### Features

- Low Power Consumption: 0.3uA (Typ)
- Maximum Output Current: 500mA
- Small Dropout Voltage 100mV@100mA (Vout=3.3V)
- PSRR=70dB@1KHz
- Input Voltage Range: 2.0V~7.0V
- Output Voltage Range: 0.8V~3.6V (customized on command in 0.05V steps)
- High Accurate: ±1.5%

## Application

- Battery-powered equipment
- Reference voltage sources
- Mobile phones

- Integrated Short-Circuit Protection
- Good Transient Response
- Over-Temperature Protection
- Support Fixed Output Voltage
- Output Current Limit
- Stable with Ceramic Capacitor
- Available Package SOT23-3 \ SOT23-5 \ SOT89-3 \ DFN1x1-4L
- RoHS Compliant and Lead (Pb) Free
- Cameras, video cameras
- Portable games
- Portable games

### Description

The WL9005 series are highly precise, low noise, positive voltage LDO regulators manufactured using CMOS processes. The series achieves high ripple rejection and low dropout and consists of a standard voltage source, an error correction, current limiter and a phase compensation circuit plus a driver transistor. Output voltage is selectable in 0.05V increments within a range of 0.8V ~ 3.6V. The series is also compatible with low ESR ceramic capacitors which give added output stability. It provides up to 500mA of output current in miniaturized packaging. The features of low quiescent current as low as  $0.3\mu$ A and almost zero disable current is ideal for powering the battery equipment to a longer service life. The other features include current limit function, Integrated Short-Circuit Protection , over temperature protection and output discharge function.

### **Application Circuits**





## **Pin Configuration**





SOT89-3L

DFN1x1-4L





### **Pin Description**

Pin No.					Die Franktien	
SOT23-3L	SOT23-5L	SOT89-3L	DFN1x1-4L	Pin Name	PIN FUNCTION	
2	1	2	4	VIN	Supply voltage input.	
1	2	1	2	GND	Ground.	
	3		3	EN	Chip Enable Control Input	
	4			NC	No Internal Connection.	
3	5	3	1	VOUT	Voltage Output.	
			5	SGND	Substrate of Chip. Leave floating or tie to GND.	

## **Order Information**

WL9005(1)(2)-(3)(4)

Designator	Symbol	Description		
12	S3/S5/P3/D4	SOT23-3L / SOT23-5L / SOT89-3L / DFN1x1-4L		
34	Integer	Output Voltage (09、10、12、15、18、25、28、30、33、36)		

Model	Marking**	Description	Package	T/R Qty
WL9005S3-XX*			SOT23-3L	3,000 PCS
WL9005S5-XX*		WL9005 0.3µA IQ ,High PSRR	SOT23-5L	3,000 PCS
WL9005P3-XX*		500mA Low-Dropout LDO	SOT89-3L	1,000 PCS
WL9005D4-XX*			DFN1x1-4L	10,000 PCS

Note: (\*) XX Represents the Output Voltage

(\*\*) For marking information, contact our sales representative directly



# Absolute Maximum Ratings (1) (2)

Parameter		Symbol	Maximum Rating	Unit	
		Vin	V <sub>SS</sub> -0.3~V <sub>SS</sub> +9.0	V	
input voita	ige	Von/off	V <sub>SS</sub> -0.3~V <sub>IN</sub> +0.3	V	
Output Cur	rent	Ιουτ	550	mA	
Output Volt	age	Vout	V <sub>SS</sub> -0.3~V <sub>IN</sub> +0.3	V	
	SOT23-3		400		
	SOT23-5	Dd	450	mW	
Power Dissipation	SOT89-3	FU	500		
	DFN1x1-4L		$\begin{array}{c c c c c c c c c c c c c c c c c c c $		
	SOT23-3		250	°C/W	
Thormal Posistance	SOT23-5	R <sub>0JA</sub> <sup>(3)</sup>	$\begin{array}{c c} & \text{Maximum Rating} \\ \hline \text{Maximum Rating} \\ \hline \text{Maximum Rating} \\ \hline \text{V}_{SS} - 0.3 \sim \text{V}_{SS} + 9.0 \\ \hline \text{V}_{SS} - 0.3 \sim \text{V}_{IN} + 0.3 \\ \hline 550 \\ \hline \text{V}_{SS} - 0.3 \sim \text{V}_{IN} + 0.3 \\ \hline 400 \\ \hline 400 \\ \hline 450 \\ \hline 500 \\ \hline 400 \\ \hline 250 \\ \hline 100 \\ \hline 250 \\ \hline 250 \\ \hline -40 \sim 85 \\ \hline -40 \sim 125 \\ \hline \text{sr} & 260 ^{\circ}\text{C}, 10\text{s} \end{array}$	°C/W	
	SOT89-3	(lunction-to-ambient thermal resistance)		°C/W	
	DFN1x1-4L		250	°C/W	
Operating Temperature		Topr	-40~85	°C	
Storage Temp	erature	Tstg	-40~125	°C	
Soldering Tempera	ture & Time	Tsolder	<b>260</b> ℃, <b>10</b> s		

Note (1): Exceeding these ratings may damage the device.

Note (2): The device is not guaranteed to function outside of its operating conditions

Note (3): The package thermal impedance is calculated in accordance to JESD 51-7.

#### **ESD Ratings**

Item	Description	Value	Unit
	Human Body Model (HBM)		
V(ESD-HBM)	ANSI/ESDA/JEDEC JS-001-2014	±4000	V
	Classification, Class: 2 Charged Device Mode (CDM)		
	Charged Device Mode (CDM)		
V(ESD-CDM)	ANSI/ESDA/JEDEC JS-002-2014	±200	V
	Human Body Model (HBM) ANSI/ESDA/JEDEC JS-001-2014 Classification, Class: 2 Charged Device Mode (CDM) ANSI/ESDA/JEDEC JS-002-2014 Classification, Class: C0b JEDEC STANDARD NO.78E APRIL 2016 Temperature Classification, Class: I		
	JEDEC STANDARD NO.78E APRIL 2016	1150	m۸
ILATCH-UP	Temperature Classification, Class: I	±4000 ±200 ±150	mА

ESD testing is performed according to the respective JESD22 JEDEC standard. The human body model is a 100 pF capacitor discharged through a  $1.5k\Omega$  resistor into each pin. The machine model is a 200pF capacitor discharged directly into each pin.

#### **Recommended Operating Conditions**

Parameter	MIN.	MAX.	Units
Supply voltage at VIN	2.0	7.0	V
Operating junction temperature range, Tj	-40	125	°C
Operating free air temperature range, TA	-25	85	°C

Note : All limits specified at room temperature (TA = 25°C) unless otherwise specified. All room temperature limits are 100% production tested. All limits at temperature extremes are ensured through correlation using standard Statistical Quality Control (SQC) methods. All limits are used to calculate Average Outgoing Quality Level (AOQL).



## **Electrical Characteristics**

(TestConditions: VIN=4.3V. VOUT=3.3)	CIN=10uF. COUT=10uF.TA=25°	C. unless otherwise specified.)

Parameter	Symbol	Conditions	Min	Тур	Max	Units
Input Voltage	Vin		2.0	_	7.0	V
Supply Current	lq	Vin > Vout ,EN=Vin Iload=0mA	_	0.3	0.7	uA
Standby Current	ISTBY	Ven = 0	—		0.1	uA
Output Voltage	Vout	V <sub>IN</sub> =V <sub>set</sub> +1.0V Iout=100mA	Vset*0.985	Vset	Vset*1.015	V
Maximum Output Current	lout(Max)	VIN=VOUT+1.0V	_	500	_	mA
		Ιουτ <b>=100mA</b>	—	100	—	m\/
	VDROP	Ιουτ <b>=200mA</b>	Win   2.0   — ()	220	—	IIIV
Line Regulation	ΔVουτ <b>/</b> ΔVin•Vout	Iouτ=10mA (Vset+0.5v)≦Vin≦7.0V	_	0.1	_	%/V
Load Regulation	Δνουτ	V <sub>IN</sub> =V <sub>set</sub> +1.0V 1mA≦Iouт≦100mA	_	20	_	mV
Current Limit	Ілміт		_	550	_	mA
Short Current	Ishort	RL=1Ω		90		mA
Power Supply		VIN=Vset+1.0V f=1KHz,Iout= 100mA	_	70	_	dB
Rejection Rate	PORK	V <sub>IN</sub> =V <sub>set</sub> +1.0V f=10KHz,Iоuт= 100mA	VIN=Vset+1.0V =10KHz,Iout= 100mA	65	_	dB
EN Threshold	VIL	VIN=3V~ 5.5V, Shutdown	—	_	0.4	V
Voltage	Vін	VIN=3V~ 5.5V, Start-Up	1.2			V
Output Noise Voltage	емо	Со∪т=1uF BW = 100Hz~10kHz	_	100	_	uVrms
Output Voltage Temperature Coefficient	ΔVουτ/ ΔΤ•Vουτ	Ιουτ <b>=30mA</b>	_	±100	_	<b>ppm/</b> ℃
Thermal Shutdown Temperature	Tsd		—	160	_	°C
Thermal Shutdown Hysteresis	ΔTsd		_	20	_	°C

Note: (1) Dropout Voltage is the voltage difference between the input and the output at which the output voltage drops 2% below its nominal value.



### **Typical Performance Characteristics**

Test Condition:  $T_{A=}25^{\circ}C$ , unless otherwise note

#### 1、VOUT vs TEMP



#### 3、Load Regulation



#### 5、Dropout Voltage vs Load Current







#### 4、Line Regulation







Note: (%)IQ refers to the working current when the chip is no-load, only when Vin >vout The chip will have a very low working current, the above diagram is for Vout 1.5v Measured Curve, when Vin<Vout, the chip is in an abnormal state that can not reach the intended output, therefore, the operating current will increase significantly. For applications where IQ requirements are strict, make sure the chip stops working when Vin <Vout.



#### 7、Load Transient Response



#### 9、Power-On



#### 11、Enable



#### 8、Short Output & Over-Current Response



#### 10、Power-Off



#### 12、Disable





### **Function Block Diagram**



### **Application Guideline**

#### **Input Capacitor**

A 1 $\mu$ F ceramic capacitor is recommended to connect between V<sub>DD</sub> and GND pins to decouple input power supply glitch and noise. The amount of the capacitance may be increased without limit. This input capacitor must be located as close as possible to the device to assure input stability and less noise. For PCB layout, a wide copper trace is required for both VIN and GND.

#### **Output Capacitor**

An output capacitor is required for the stability of the LDO. The recommended output capacitance is  $10\mu$ F, ceramic capacitor is recommended, and temperature characteristics are X7R or X5R. Higher capacitance values help to improve load/line transient response. The output capacitance may be increased to keep low undershoot/overshoot. Place output capacitor as close as possible to VOUT and GND pins.

#### **Dropout Voltage**

The dropout voltage refers to the voltage difference between the VIN and VOUT pins while operating at specific output current. The dropout voltage VDROP also can be expressed as the voltage drop on the pass-FET at specific output current (IRATED) while the pass-FET is fully operating at ohmic



region and the pass-FET can be characterized as resistance RDS(ON). Thus the dropout voltage can be defined as (VDROP = VIN – VOUT = RDS(ON) x IRATED). Fornormal operation, the suggested LDO operating range is (VIN > VOUT + VDROP) for good transient response and PSRR ability. Vice versa, while operating at the ohmic region will degrade the performance severely.

#### **Thermal Application**

For continuous operation, do not exceed the absolute maximum junction temperature. The maximum power dissipation depends on the thermal resistance of the IC package, PCB layout, rate of surrounding airflow, and difference between junction and ambient temperature. The maximum power dissipation can be calculated as below: TA=25°C, PCB,

The max PD= (125°C - 25°C) / (Thermal Resistance °C/W)

Power dissipation (PD) is equal to the product of the output current and the voltage drop across the output pass element, as shown in the equation below:

 $PD = (VIN - VOUT) \times IOUT$ 

#### Layout Consideration

By placing input and output capacitors on the same side of the PCB as the LDO, and placing them as close as is practical to the package can achieve the best performance. The ground connections for input and output capacitors must be back to the WL9005 ground pin using as wide and as short of a copper trace as is practical.Connections using long trace lengths, narrow trace widths, and/or connections through via must be avoided. These add parasitic inductances and resistance that results in worse performance especially during transient conditions.



SOT23-3L







Symbol	Dimensions Ir	n Millimeters	Dimensions	In Inches
Symbol	Min	Max	Min	Max
A	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.300	0.500	0.012	0.020
C	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
E	1.500	1.700	0.059	0.067
E1	2.650	2.950	0.104	0.116
e	0.950	(BSC)	0.037(	BSC)
e1	1.800	2.000	0.071	0.079
L	0.300	0.600	0.012	0.024
θ	0°	8°	0°	8°



### SOT89-3L



Cumhal	Dimensions	In Millimeters	<b>Dimensions In Inches</b>	
Symbol	Min.	Max.	Min.	Max.
A	1.400	1.600	0.055	0.063
b	0.320	0.520	0.013	0.020
b1	0.400	0.580	0.016	0.023
С	0.350	0.440	0.014	0.017
D	4.400	4.600	0.173	0.181
D1	1.550 REF.		0.061	REF.
E	2.300	2.600	0.091	0.102
E1	3.940	4.250	0.155	0.167
е	1.50	1.500 TYP.		TYP.
e1	3.000	0 TYP.	0.118 TYP.	
L	0.900	1.200	0.035	0.047



SOT23-5L





TOP VIEW

TOP VIEW

RECOMMENDED PAD LAYOUT

### RECOMMENDED PAD LAYOUT





### DFN1x1-4L





Detail A: (PIN1 shape)



Unit:mm